grands			CA
	Application No.	Applicant(s)	
Notice of Allowability	09/761,923	YANG ET AL.	*
	Examiner	Art Unit	
	Lan Vinh	1765	<u> </u>
The MAILING DATE of this communication ap All claims being allowable, PROSECUTION ON THE MERITS herewith (or previously mailed), a Notice of Allowance (PTOL-8 NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT of the Office or upon petition by the applicant. See 37 CFR 1.3	IS (OR REMAINS) CLOSED 35) or other appropriate comm RIGHTS. This application is	in this application. If not include nunication will be mailed in due	ded e course. THIS
1. This communication is responsive to <u>Amendment filed on</u>	<u>n10/20/2003</u> .		
2. The allowed claim(s) is/are <u>1-15.</u>	Ale - Commission and		
3. ⊠ The drawings filed on <u>17 January 2001</u> are accepted by 4. ⊠ Acknowledgment is made of a claim for foreign priority		or (f)	
a) ⊠ All b) ☐ Some* c) ☐ None of the:	under 35 0.5.C. § 119(a)-(d)	i or (i).	
1. Certified copies of the priority documents ha	ave been received.		
2. Certified copies of the priority documents ha	ave been received in Applicati	on No. <u>09/761923</u> .	
3. Copies of the certified copies of the priority	documents have been receive	ed in this national stage applic	ation from the
International Bureau (PCT Rule 17.2(a)).			
* Certified copies not received:			
 Acknowledgment is made of a claim for domestic priority reference was included in the first sentence of the specified. 			ce a specific
(a) The translation of the foreign language provisiona	• •		
 Acknowledgment is made of a claim for domestic priority in the first sentence of the specification or in an Application 	/ under 35 U.S.C. §§ 120 and	/or 121 since a specific refere	nce was included
Applicant has THREE MONTHS FROM THE "MAILING DATE" below. Failure to timely comply will result in ABANDONMENT			
 A SUBSTITUTE OATH OR DECLARATION must be sub INFORMAL PATENT APPLICATION (PTO-152) which g 	gives reason(s) why the oath		NOTICE OF
 CORRECTED DRAWINGS (as "replacement sheets") m (a) ☐ including changes required by the Notice of Draftsp 1) ☐ hereto or 2) ☐ to Paper No 		ew (PTO-948) attached	
(b) ☐ including changes required by the proposed drawing	a correction filed whi	ch has been approved by the	Examiner
(c) ☐ including changes required by the attached Examination		• •	
Identifying indicia such as the application number (see 37 CFF each sheet. Replacement sheet(s) should be labeled as such i			e back) of
 DEPOSIT OF and/or INFORMATION about the de- attached Examiner's comment regarding REQUIREMENT FOR 			Note the
Attachment(s)			
1☐ Notice of References Cited (PTO-892)	5∐ Notice of In	formal Patent Application (PT0	O-152)
 Notice of Draftperson's Patent Drawing Review (PTO-948) Information Disclosure Statements (PTO-1449 or PTO/SB/08 Paper No		ummary (PTO-413), Paper No	·
	/08), 7□ Examiner's	7☐ Examiner's Amendment/Comment	
4☐ Examiner's Comment Regarding Requirement for Deposit of Biological Material	8⊠ Examiner's 9⊡ Other	Statement of Reasons for Allo	wance
		Lan Vinh AU 17 65	/
		Man	

U.S. Patent and Trademark Office PTOL-37 (Rev. 11-03) Application/Control Number: 09/761,923

Art Unit: 1765

Allowable Subject Matter

1. Claims 1-15 are allowed.

The following is an examiner's statement of reasons for allowance:

Regarding claim 1, the applicants have presented a persuasive argument that the cited prior arts of record fails to disclose a method of forming an opening in a dielectric layer comprises the step of performing an ion implantation step with the mask on the undoped dielectric layer, so that a doped region is formed in the exposed portion of the undoped dielectric layer below the first opening, leaving the exposed portion of the undoped dielectric layer below the doped region undoped, wherein a depth of the doped region does not exceed a thickness of the undoped dielectric layer. The closest cited prior art of Liu et al (US 6,326,300) discloses performing an ion implantation step 26 with the mask on the undoped dielectric layer 22', so that a doped region is formed through the exposed portion of the undoped dielectric 22' layer below an opening, leaving none of the dielectric layer 22' undoped below the exposed doped region (fig. 5)

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Conclusion

2. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Lan Vinh whose telephone number is 703 305-6302. The examiner can normally be reached on M-F 8:30-5:30 PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine Norton can be reached on 703 305-2667. The fax phone number for the organization where this application or proceeding is assigned is 703 872-9310.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is 703 308-0661.

November 10, 2003